What is claimed is:

1. A method of manufacturing a lapping plate comprising:

selectively etching a metal plate; and

imbedding diamond particles into said metal plate.

2. The method of claim 1 wherein said etching step includes:

applying a photoresist layer to said metal plate; and

selectively removing photoresist from a surface of said metal plate.

3. A method of manufacturing a lapping plate comprising:

applying a photoresist layer to a metal plate;

selectively exposing areas of said photoresist layer to electromagnetic radiation;

developing said photoresist layer;

etching areas of said metal disk; and

imbedding diamond particles into non-etched areas of said metal disk.

4. The method of claim 3 wherein said selectively exposing operating includes:

providing a mask between an electromagnetic radiation source and said photoresist layer;

5. The method of claim 4 wherein said mask is a wire mesh.

6. The method of claim 4 wherein said electromagnetic radiation is ultra-violet radiation.

7. The method of claim 4 wherein said photoresist is a positive photoresist.

8. The method of claim 4 wherein said photoresist is a negative photoresist.

9. The method of claim 4 wherein said etching operation is a wet-etch operation.

10. The method of claim 4 wherein said diamond particles have a diameter less than 50 nanometers.

11. A method of fabricating a read/write head for a disk drive, comprising:

applying a photoresist layer to a metal plate;

selectively exposing areas of said photoresist layer to electromagnetic radiation;

developing said photoresist layer;

etching areas of said metal disk;

imbedding diamond particles into non-etched areas of said metal disk to create a lapping plate; and

lapping a read/write head with said lapping plate.

12. The method of claim 11 wherein said selectively exposing operating includes:

providing a mask between an electromagnetic radiation source and said photoresist layer;

13. The method of claim 12 wherein said mask is a wire mesh.

14. The method of claim 12 wherein said electromagnetic radiation is ultra-violet radiation.

15. The method of claim 12 wherein said photoresist is a positive photoresist.

16. The method of claim 12 wherein said photoresist is a negative photoresist.

17. The method of claim 12 wherein said etching operation is a wet-etch operation.

18. The method of claim 12 wherein said diamond particles have a diameter less than 50 nanometers.

19. The method of claim 18 wherein said read/write head is a GMR read/write head.

20. The method of claim 18 wherein a pole tip recession for said GMR read/write head is between 2 and 3 nanometers.

21. A lapping plate comprising:

a metal plate including a plurality of etched areas, said etched areas formed from an etching operation through a developed photoresist mask; and

diamond particles imbedded into non-etched areas of the metal plate.

22. The lapping plate of claim 21 wherein said photoresist is a positive photoresist.

23. The lapping plate of claim 21 wherein said photoresist is a negative photoresist.

24. The lapping plate of claim 21 wherein said metal plate is wet-etched.

25. The lapping plate of claim 21 wherein said diamond particles have a diameter less than 50 nanometers.